### Vishay Semiconductors



## Symbols and Terminology

A Anode, anode terminal

A Ampere, SI unit of electrical current

A Radiant sensitive area, that area which is radiant

sensitive for a specified range

a **Distance**, e.g. between the emitter (source) and

the detector

B Base, base terminal

BER Bit Error Rate

bit/s Data rate or signaling rate

 $1000 \text{ bit/s} = 1 \text{ kbit/s}, 10^6 \text{ bit/s} = 1 \text{ Mbit/s}$ 

C Capacitance, unit: F (farad) = C/V

C Coulomb,  $C = s \times A$ 

C Cathode, cathode terminal

C Collector, collector terminal

°C **Degree Celsius,** Celsius temperature, symbol t, and is defined by the quantity equation  $t = T - T_0$ . The unit of Celsius temperature is the degree Celsius, symbol °C. The numerical value of a Celsius temperature t expressed in degrees

Celsius is given by  $t/^{\circ}C = T/K - 273.15$ 

It follows from the definition of t that the degree Celsius is equal in magnitude to the Kelvin, which in turn implies that the numerical value of a given temperature difference or temperature interval whose value is expressed in the unit degree Celsius (°C) is equal to the numerical value of the same difference or interval when its value is expressed in the unit Kelvin (K).

C<sub>CEO</sub>

Collector emitter capacitance, Capacitance between the collector and the emitter with open base cd

Candela, SI unit of luminous intensity. The

candela is the luminous intensity, in a given direction, of a source that emits monochromatic radiation of frequency 540 Hz x 1012 Hz and that has a radiant intensity in that direction of 1/683 W per steradian. ( $16^{th}$  General Conference of Weights and Measures, 1979), 1 cd = 1 lm · sr <sup>-1</sup>

C<sub>D</sub> **Diode capacitance**, total capacitance effective between the diode terminals due to case, junction and parasitic capacitances

Cj **Junction capacitance**, capacitance due to a p-n junction of a diode, decreases with increasing reverse voltage

d Apparent (of virtual) source size (of an emitter), the measured diameter of an optical source used to calculate the eye safety laser class of the source. See IEC 60825-1 and EN ISO 11146-1

D\* **Detectivity**  $\sqrt{A/NEP}$ 

E Emitter, Emitter terminal (phototransistor)

 $\mathsf{E}_\mathsf{A}$  Illumination at standard illuminant  $\mathsf{A}$ , according to DIN 5033 and IEC 306-1, illumination emitted from a tungsten filament lamp with a color temperature  $\mathsf{T}_\mathsf{f} = 2855.6 \; \mathsf{K}$ , which is equivalent to

standard illuminant A, unit: lx (Lux) or klx

E<sub>A amb</sub> Ambient illumination at standard illuminant A

echo-off Unprecise term to describe the behavior of the output of IrDA® transceivers during transmission. "Echo-off" means that by blocking the receiver the output RXD is guiet during transmission

echo-on Unprecise term to describe the behavior of the output of IrDA® transceivers during transmission. "Echo-on" means that the receiver output RXD is active but often undefined during transmission. For correct data reception after transmission the receiver channel must be cleared during the

latency period

$$E_{e} = \frac{d\Phi_{e}}{dA} = \int_{2\pi sr} \left( L_{e} \cdot \cos\theta \cdot d\Omega \right)$$

unit: W · m<sup>-2</sup>

E<sub>v</sub>, E **Illuminance** (at a point of a surface), quotient of the luminous flux  $d\Phi_v$  incident on an element of the surface containing the point, by the area dA of that element. Equivalent definition. Integral, taken over the hemisphere visible from the givenpoint, of the expression  $L_v \cdot \cos\theta \cdot d\Omega$ , where  $L_v$  is the luminance at the given point in the various directions of the incident elementary beams of solid angle  $d\Omega$ , and  $\theta$  is the angle between any of these beams and the normal to the surface at the given point

$$\boldsymbol{E}_{\boldsymbol{V}} = \frac{d\boldsymbol{\Phi}_{\boldsymbol{V}}}{\text{dA}} = \underset{2\pi sr}{\int} \left(\boldsymbol{L}_{\boldsymbol{V}} \cdot \boldsymbol{cos}\,\boldsymbol{\theta} \cdot \text{d}\boldsymbol{\Omega}\right)$$

unit:  $lx = lm \cdot m^{-2}$ 

F Farad, unit: F = C/V

 $f_c$ ,  $f_{cd}$ 

Frequency, unit: s<sup>-1</sup>, Hz (Hertz)

**Cut-off frequency** - detector devices, the frequency at which, for constant signal modulation depth of the input radiant power, the demodulated signal power has decreased to  $\frac{1}{2}$  of its low frequency value. Example: The incident radiation generates a photocurrent or a photo voltage 0.707 times the value of radiation at f = 1 kHz

(3 dB signal drop, other references may occur as e.g. 6 dB or 10 dB)



### Symbols and Terminology

## Vishay Semiconductors

f <sub>s</sub>	Switching frequency	IRED	Infrared emitting diode, solid state device
FIR	Fast infrared, as SIR, data rate 4 Mbit/s		embodying a p-n junction, emitting infrared radiation when excited by an electric current. See
l <sub>a</sub>	Light current, general: current which flows through a device due to irradiation/illumination		also LED: solid state device embodying a p-n
$I_{B}$	Base current		junction, emitting optical radiation when excited by
I <sub>BM</sub>	Base peak current	ı	an electric current.
I <sub>C</sub>	Collector current	I <sub>ro</sub>	Reverse dark current, dark current, reverse current flowing through a photoelectric device in
I <sub>ca</sub>	Collector light current, collector current under		the absence of irradiation
04	irradiation. Collector current which flows at a	IRPHY	Version 1.0, SIR IrDA®, data communication
	specified illumination/irradiation	INFIII	specification covering data rates from 2.4 kbit/s
$I_{CEO}$	Collector dark current, with open base,		to 115.2 kbit/s and a guaranteed operating range
	collector emitter dark current. For radiant sensitive		more than one meter in a cone of ± 15°
	devices with open base and without	IRPHY	Version 1.1, MIR and FIR were implemented in the
	illumination/radiation (E = 0)		IrDA® standard with the version 1.1, replacing
I <sub>CM</sub>	Repetitive peak collector current		version 1.0
idle	Mode of operation where the device (e.g. a	IRPHY	Version 1.2, added the SIR low power standard to
	transceiver) is fully operational and expecting to receive a signal for operation e.g in case of a		the IrDA® standard, replacing version 1.1. The SIR
	transceiver waiting to receive an optical input or to		low power standard describes a current saving
	send an optical output as response to an applied		implementation with reduced range (min. 20 cm to
	electrical signal.		other low power devices and min. 30 cm to full
l <sub>e</sub> , I	Radiant intensity (of a source, in a given		range devices).
	direction), quotient of the radiant flux d $\Phi_{\rm e}$ leaving	IRPHY	Version 1.3, extended the low power option to the
	the source and propagated in the element of solid		higher bit rates of MIR and FIR replacing version 1.2.
	angle $d\Omega$ containing the given direction, by the	IRPHY	Version 1.4, VFIR was added, replacing version 1.3
	element of solid angle. $I_e = d\Phi_e/d\Omega$ , unit: $W \cdot sr^{-1}$	$I_{SB}$	Quiescent current
	Note: The radiant intensity $I_e$ of emitters is typically	$I_{SD}$	Supply current in dark ambient
	measured with an angle < 0.01 sr on mechanical	I <sub>SH</sub>	Supply current in bright ambient
	axis or off-axis in the maximum of the irradiation	I <sub>v</sub> , I	Luminous intensity (of a source, in a given
	pattern.	• ·	direction), quotient of the luminous flux $d\Phi_v$ leaving
$I_F$	Continuous forward current, the current flowing		the source and propagated in the element of solid
	through a diode in the forward direction		angle $d\Omega$ containing the given direction, by the
$I_{FAV}$	Average (mean) forward current		element of solid angle. $I_e = d\Phi_V/d\Omega$ , unit: $cd \cdot sr^{-1}$
I <sub>FM</sub>	Peak forward current		Note: The luminous intensity $I_v$ of emitters is typically measured with an angle < 0.01 sr on
I <sub>FSM</sub>	Surge forward current		mechanical axis or off-axis in the maximum of the
l <sub>k</sub>	Short-circuit current, that value of the current		irradiation pattern.
	which flows when a photovoltaic cell or a	K	luminous efficacy of radiation, quotient of the
	photodiode is short circuited ( $R_L \ll R_i$ ) at its terminals		luminous flux $\Phi_v$ by the corresponding radiant flux
I <sub>o</sub>	DC output current		$\Phi_e$ : K = $\Phi_v / \Phi_e$ , unit: Im · W <sup>-1</sup>
I <sub>ph</sub>	Photocurrent, that part of the output current of a		Note: When applied to monochromatic radiations,
-рп	photoelectric detector, which is caused by incident		the maximum value of $K(\lambda)$ is denoted by the
	radiation.		symbol K <sub>m</sub> .
$I_R$	Reverse current, leakage current, current which		$K_m = 683 \text{ Im} \cdot \text{W}^{-1} \text{ for } v_m = 540 \text{ x } 10^{12} \text{ Hz}$ ( $\lambda_m \approx 555 \text{ nm}$ ) for photopic vision.
	flows through a reverse biased semiconductor		$K'_m = 1700 \text{ Im} \cdot W^{-1} \text{ for } \lambda'_m \approx 507 \text{ nm for scotopic}$
	p-n-junction		vision. For other wavelengths:
IR	Abbreviation for infrared		$K(\lambda) = K_m V(\lambda)$ and $K'(\lambda) = K'_m V'(\lambda)$
I <sub>ra</sub>	Reverse current under irradiation, reverse light	K	Kelvin, SI unit of thermodynamic temperature, is
	current which flows due to a specified		the fraction 1/273.15 of the thermodynamic
	irradiation/illumination in a photoelectric device		temperature of the triple point of water
	$I_{ra} = I_{ro} + I_{ph}$		(13th CGPM (1967), Resolution 4). The unit Kelvin
IrDA <sup>®</sup>	Infrared Data Association, no profit organization		and its symbol K should be used to express an
	generating infrared data communication standards		interval or a difference of temperature.
			Note: In addition to the thermodynamic

### Vishay Semiconductors

#### Symbols and Terminology



temperature (symbol T), expressed in Kelvins, use is also made of Celsius temperature (symbol t) defined by the equation  $t=T-T_0$ , where  $T_0=273.15~\rm K$  by definition. To express Celsius temperature, the unit "degree Celsius", which is equal to the unit "Kelvin" is used; in this case, "degree Celsius" is a special name used in place of "Kelvin". An interval or difference of Celsius temperature can, however, be expressed in Kelvins as well as in degrees Celsius.

Latency Receiver latency allowance (in ms or μs) is the maximum time after a node ceases transmitting before the node's receiving recovers its specified sensitivity

LED and IRED

Light Emitting Diode, LED: solid state device embodying a p-n junction, emitting optical radiation when excited by an electric current. The term LED is correct only for visible radiation, because light is defined as visible radiation (see Radiation and Light). For infrared emitting diodes the term IRED is the correct term. Nevertheless it is common but not correct to use "LED" also for IREDs.

L<sub>e</sub>; L **Radiance** (in a given direction, at a given point of a real or imaginary surface).

Quantity defined by the formula

$$L_e = \frac{\text{d}\Phi_v}{\text{d}A \cdot \text{cos}\,\theta \cdot \text{d}\Omega} \quad , \label{eq:left_energy}$$

where  $d\Phi_e$  is the radiant flux transmitted by an elementary beam passing through the given point and propagating in the solid angle  $d\Omega$  containing the given direction; dA is the area of a section of that beam containing the given point;  $\theta$  is the angle between the normal to that section and the direction of the beam, unit: W  $\cdot$  m $^{-2} \cdot$  sr $^{-1}$ 

Im Lumen, unit for luminous flux

lx **Lux**, unit for illuminance

m Meter, SI unit of length

Me; M Radiant exitance (at a point of a surface) - Quotient of the radiant flux  $d\Phi_e$  leaving an element of the surface containing the point, by the area dA of that element. Equivalent definition. Integral, taken over the hemisphere visible from the given point, of the expression  $L_e \cdot cos\theta \cdot d\Omega,$  where  $L_e$  is the radiance at the given point in the various directions of the emitted elementary beams of solid angle  $d\Omega,$  and  $\theta$  is the angle between any of these beams and the normal to the surface at the given point.

$$M_{e} = \frac{d\Phi_{e}}{dA} = \int_{2\pi sr} L_{e} \cdot cos\theta \cdot d\Omega$$
unit: W · m<sup>-2</sup>

MIR **Medium speed IR,** as SIR, with the data rate 576 kbit/s to 1152 kbit/s

Mode Electrical input or output port of a transceiver device to set the receiver bandwidth

N.A. Numerical Aperture, N.A. =  $\sin \alpha/2$ 

Term used for the characteristic of sensitivity or intensity angles of fiber optics and objectives

NEP Noise equivalent power

P<sub>tot</sub> Total power dissipation

P<sub>v</sub> Power dissipation, general

Radiation and Light

**Visible radiation**, any optical radiation capable of causing a visual sensation directly.

Note: There are no precise limits for the spectral range of visible radiation since they depend upon the amount of radiant power reaching the retina and the responsivity of the observer. The lower limit is generally taken between 360 nm and 400 nm and the upper limit between 760 nm and 830 nm.

Radiation and Light

**Optical radiation**, electromagnetic radiation at wavelengths between the region of transition to X-rays ( $\lambda = 1$  nm) and the region of transition to radio waves ( $\lambda = 1$  mm)

Radiation and Light IR

**Infrared radiation**, optical radiation for which the wavelengths are longer than those for visible radiation.

Note: For infrared radiation, the range between 780 nm and 1 mm is commonly sub-divided into:

IR-A 780 nm to 1400 nm IR-B 1.4  $\mu$ m to 3  $\mu$ m

 $R_D \qquad \text{IR-C 3 } \mu \text{m to 1 mm}$   $R_D \qquad \text{Dark resistance}$ 

R<sub>F</sub> Feedback resistor

R<sub>i</sub> Internal resistance

R<sub>is</sub> Isolation resistance

R<sub>L</sub> Load resistance

R<sub>S</sub> Serial resistance

R<sub>sh</sub> **Shunt resistance**, the shunt resistance of a detector diode is the dynamic resistance of the diode at zero bias. Typically it is measured at a voltage of 10 mV forward or reverse, or peak-to-peak

R<sub>thJA</sub> Thermal resistance, junction to ambient

R<sub>thJC</sub> Thermal resistance, junction to case

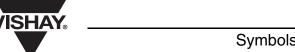
RXD Electrical data output port of a transceiver device

s **Second**, SI-unit of time 1 h = 60 min = 3600 s

S Absolute sensitivity

Ratio of the output value Y of a radiant-sensitive device to the input value X of a physical quantity: S = Y/X, units: e.g. A/Ix, A/W,  $A/(W/m^2)$ 

 $s(\lambda_p)$  Spectral sensitivity at a wavelength  $\lambda_p$ 



### Symbols and Terminology Vishay Semiconductors

s( $\lambda$ ) Absolute spectral sensitivity at a wavelength  $\lambda$ , the ratio of the output quantity y to the radiant input quantity x in the range of wavelengths

 $\lambda$  to  $\lambda + \Delta\lambda$ 

 $s(\lambda) = dy(\lambda)/dx(\lambda)$ 

E.g., the radiant power  $\Phi_e(\lambda)$  at a specified wavelength  $\lambda$  falls on the radiationsensitive area of a detector and generates a photocurrent  $I_{ph} \cdot s(\lambda)$  is the ratio between the generated photocurrent lph and the radiant power  $\Phi_e(\lambda)$  which falls on the detector.  $s(\lambda) = I_{ph} / \Phi_e(\lambda)$ , unit: A/W

 $s(\lambda)_{rel} \qquad \begin{array}{ll} \textbf{Spectral sensitivity, relative,} \ \text{ratio of the spectral} \\ \text{sensitivity} \ s(\lambda) \ \text{at any considered wavelength to} \\ \text{the spectral sensitivity} \ s(\lambda_0) \ \text{at a certain} \\ \text{wavelength} \ \lambda_0 \ \text{taken as a reference} \\ \text{s}(\lambda)_{rel} = s(\lambda)/s(\lambda_0) \end{array}$ 

 $\begin{array}{ll} s(\lambda_0) & \textbf{Spectral sensitivity} \text{ at a reference wavelength } \lambda_0 \\ \text{SC} & \text{Electrical input port of a transceiver device to set} \\ & \text{the receiver sensitivity} \end{array}$ 

SD Electrical input port of a transceiver device to shut down the transceiver

#### Shutdown

Mode of operation where a device is switched to a sleep mode (shut down) by an external signal or after a quiescent period keeping some functions alive to be prepared for a fast transition to operating mode. Might be in some cases identical with "standby"

SIR **Serial Infrared**, term used by IrDA® to describe infrared data transmission up to and including 115.2 kbit/s. SIR IrDA® data communication covers 2.4 kbit/s to 115.2 kbit/s, equivalent to the basic serial infrared standard introduced with the physical layer version IrPhy version 1.0

#### Split power supply

Term for using **separated power supplies** for different functions in transceivers. Receiver circuits need well-controlled supply voltages. IRED drivers do not need a controlled supply voltage but need much higher currents. Therefore it safes cost not to control the IRED current supply and have a separated supply. For that some modified design rules have to be taken into account for designing the ASIC. This is used in nearly all Vishay transceivers and is described in US-Patent no. 6,157,476

sr **Steradian** (sr), SI unit of solid angle  $\Omega$ . Solid angle that, having its vertex at the centre of a sphere, cuts off an area of the surface of the sphere equal to that of a square with sides of length equal to the radius of the sphere. (ISO, 31/1-2.1, 1978)

Example: The unity solid angle, in terms of geometry, is the angle subtended at the center of a sphere by an area on its surface numerically equal to the square of the radius (see figures below). Other than the figures might suggest, the

shape of the area does not matter at all. Any shape on the surface of the sphere that holds the same area will define a solid angle of the same size. The unit of the solid angle is the **steradian (sr)**. Mathematically, the solid angle is dimensionless, but for practical reasons, the steradian is assigned.

#### Standby

Mode of operation where a device is prepared to be quickly switched into an idle or operating mode by an external signal.

- T **Period of time** (duration)
- T Temperature, 0 K = 273.15 °C, unit: K (Kelvin)
- t **Temperature**, °C (degree Celsius). Instead of t sometimes T is used not to mix up temperature T with time t
- t Time
- T<sub>amb</sub> **Ambient temperature,** if self-heating is significant: temperature of the surrounding air below the device, under conditions of thermal equilibrium. If self-heating is insignificant: air temperature in the surroundings of the device
- T<sub>amb</sub> Ambient temperature range, as an absolute maximum rating: the maximum permissible ambient temperature range
- T<sub>C</sub> **Temperature coefficient,** the ratio of the relative change of an electrical quantity to the change in temperature (ΔT) which causes it under otherwise constant operating conditions
- T<sub>C</sub> Colour temperature (BE), the temperature of a Planckian radiator whose radiation has the same chromaticity as that of a given stimulus, unit: K Note: The reciprocal colour temperature is also used, unit K-1 (BE).
- T<sub>case</sub>

  Case temperature, the temperature measured at a specified point on the case of a semiconductor device. Unless otherwise stated, this temperature is given as the temperature of the mounting base for devices with metal can
- t<sub>d</sub> Delay time
- t<sub>f</sub> **Fall time,** the time interval between the upper specified value and the lower specified value on the trailing edge of the pulse.

Note: It is common to use a 90 % value of the signal for the upper specified value and a 10 % value for the lower specified value.

- T<sub>j</sub> **Junction temperature,** the spatial mean value of the temperature during operation. In the case of phototransistors, it is mainly the temperature of the collector junction because its inherent temperature is the maximum.
- toff Turn-off time, the time interval between the upper specified value on the trailing edge of the applied input pulse and the lower specified value an the trailing edge of the output pulse.  $t_{\text{off}} = t_{\text{d(off)}} + t_{\text{f}}$

### Vishay Semiconductors

#### Symbols and Terminology



 $t_{on}$  **Turn-on time**, the time interval between the lower specified value on the trailing edge of the applied input pulse and the upper specified value an the trailing edge of the output pulse.  $t_{on} = t_{d(on)} + t_f$  **t**p **Pulse duration**, the time interval between the

**Pulse duration,** the time interval between the specified value on the leading edge of the pulse and the specified value and the trailing edge of the output pulse.

Note: In most cases the specified value is 50 % of the signal

t<sub>pi</sub> Input pulse duration

t<sub>po</sub> Output pulse duration

t<sub>r</sub> Rise time, the time interval between the lower specified value and the upper specified value on the trailing edge of the pulse.

Note: It is common to use a 90 % value of the signal for the upper specified value and a 10 % value for the lower specified value  $t_{\rm s}$  storage time

t<sub>s</sub> Storage time

T<sub>sd</sub> **Soldering temperature,** maximum allowable temperature for soldering with a specified distance from the case and its duration

T<sub>stg</sub> Storage temperature range, the temperature range at which the device may be stored or transported without any applied voltage

TXD Electrical data input port of a transceiver device

V Volt

V(λ) **Standard luminous efficiency function** for photopic vision (relative human eye sensitivity)

 $V(\lambda)$ ,  $V'(\lambda)$ 

**Spectral luminous efficiency** (of a monochromatic radiation of wavelength  $\lambda$ );  $V(\lambda)$  for photopic vision;  $V'(\lambda)$  for scotopic vision).

Ratio of the radiant flux at wavelength  $\lambda_m$  to that at wavelength  $\lambda$  such that both radiations produce equally intense luminous sensations under specified photometric conditions and  $\lambda_m$  is chosen so that the maximum value of this ratio is equal to 1

V<sub>BEO</sub> Base emitter voltage, open collector

V<sub>(BR)</sub> Breakdown voltage, reverse voltage at which a small increase in voltage results in a sharp rise of reverse current. It is given in technical data sheets for a specified current

 $V_{(BR)}$  CEO Collector emitter breakdown voltage, open base

 $V_{(BR)EBO}$  Emitter base breakdown voltage, open collector

V<sub>(BR)ECO</sub> Emitter collector breakdown voltage, open base

V<sub>CBO</sub>
Collector-base voltage, open emitter, generally, reverse biasing is carried out by applying a voltage to any of two terminals of a transistor in such a way that one of the junctions operates in reverse direction, whereas the third terminal (second junction) is specified separately.

V<sub>CC</sub> Supply voltage (positive) V<sub>CE</sub> Collector emitter voltage

 $V_{CEO}$  Collector emitter voltage, open base ( $I_B = 0$ ) Collector emitter saturation voltage, the saturation voltage is the DC voltage between collector and emitter for specified (saturation) conditions, i.e.,  $I_C$  and  $E_V$  ( $E_e$  or  $I_B$ ), whereas the operating point is within the saturation region.

V<sub>dd</sub> Supply voltage (positive)

V<sub>EBO</sub> Emitter base voltage, open collector V<sub>ECO</sub> Emitter collector voltage, open base

V<sub>F</sub> **Forward voltage**, the voltage across the diode terminals which results from the flow of current in the forward direction

VFIR As SIR, data rate 16 Mbit/s

 $V_{logic}$  Reference voltage for digital data communication

ports

V<sub>no</sub> Signal-to-noise ratio

V<sub>O</sub> Output voltage

 $\Delta V_{\mathrm{O}}$  Output voltage change (differential output voltage)

V<sub>OC</sub> **Open circuit voltage,** the voltage measured between the photovoltaic cell or photodiode terminals at a specified irradiance/illuminance (high impedance voltmeter!)

 $V_{OH}$  Output voltage high

V<sub>OL</sub> Output voltage low

V<sub>ph</sub> **Photovoltage**, the voltage generated between the photovoltaic cell or photodiode terminals due to irradiation/ illumination

V<sub>R</sub> Reverse voltage (of a junction), applied voltage such that the current flows in the reverse direction

V<sub>R</sub> Reverse (breakdown) voltage, the voltage drop which results from the flow of a defined reverse current

V<sub>S</sub> Supply voltage

V<sub>ss</sub> (Most negative) **supply voltage** (in most cases:

 $\pm~\phi_{1/2}$   $\,$  Angle of half transmission distance

 $\eta \qquad \qquad \text{Quantum efficiency}$ 

 $\theta_{1/2}$ ;  $\pm \varphi = \alpha/2$ 

Half-intensity angle, in a radiation diagram, the angle within which the radiant (or luminous) intensity is greater than or equal to half of the maximum intensity.

Note: IEC 60747-5-1 is using  $\theta_{1/2}$ . In Vishay datasheets mostly  $\pm \phi = \alpha/2$  is used

 $\theta_{1/2}$ ;  $\pm \varphi = \alpha/2$ 

**Half-sensitivity angle,** in a sensitivity diagram, the angle within which the sensitivity is greater than or equal to half of the maximum sensitivity. Note: IEC 60747-5-1 is using  $\theta_{1/2}$ . In Vishay datasheets mostly  $\pm \phi = \alpha/2$  is used





Vishay Semiconductors

Solid Ω angle, steradian see sr, IEC 60050(845)-definition. The space enclosed by rays, which emerge from a single point and lead to all the points of a closed curve. If it is assumed that the apex of the cone formed in this way is the center of a sphere with radius r and that the cone intersects with the surface of the sphere, then the size of the surface area (A) of the sphere subtending the cone is a measure of the solid angle  $\Omega$ .  $\Omega = A/r^2$ . The full sphere is equivalent to  $4\pi sr.$  A cone with an angle of  $\alpha/2$  forms a solid angle of  $\Omega = 2 \pi (1 - \cos \alpha/2) = 4 \pi \sin^2 \alpha/4$ , unit: sr

Δλ Range of spectral bandwidth (50 %), the range of wavelengths where the spectral sensitivity or spectral emission remains within 50 % of the maximum value

 $\Phi_e$ ;  $\Phi$ ; P

Radiant flux; radiant power, power emitted, transmitted or received in the form of radiation. unit: W. W = Watt

 $\Phi_{
m V};\Phi;$  Luminous flux, quantity derived from radiant flux  $\Phi_{
m e}$  by evaluating the radiation according to its action upon the CIE standard photometric

observer. For photopic vision

$$\Phi_{v} \, = \, K_{m} J_{0}^{\infty} \frac{d\Phi_{e} \lambda}{d\lambda} \cdot V(\lambda) d\lambda, \label{eq:phivarphi}$$

where  $\frac{\text{d}\Phi_{\text{e}}\lambda}{\text{d}\lambda}$  is the spectral distribution of the

radiant flux and V( $\lambda$ ) is the spectral luminous efficiency, unit : Im, Im: lumen, K<sub>m</sub> = 683 Im/W: Note: For the values of K<sub>m</sub> (photopic vision) and K'm (scotopic vision), see IEC 60050 (845-01-56).

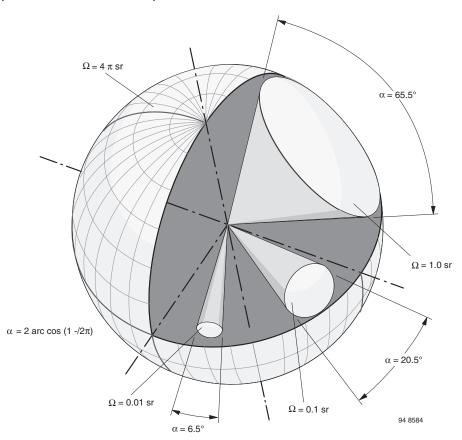
Wavelength, general

Centroid wavelength, centroid wavelength  $\lambda_c$  of a spectral distribution, which is calculated as "centre of gravity wavelength" according to

$$\lambda_{c} = \int_{\lambda_{1}}^{\lambda_{2}} \lambda \cdot S_{x}(\lambda) d\lambda / \int_{\lambda_{1}}^{\lambda_{2}} S_{x} \cdot (\lambda) d\lambda$$

Dominant wavelength

Wavelength of peak sensitivity or peak emission



 $\lambda_{D}$ 

 $\lambda_p$ 

Fig. 1

Vishay Semiconductors

Symbols and Terminology



#### **DEFINITIONS**

#### **Databook Nomenclature**

The nomenclature, symbols, abbreviations and terms inside the Vishay Semiconductors data book is based on ISO and IEC standards.

The special optoelectronic terms and definitions are referring to the IEC Multilingual Dictionary (Electricity, Electronics and Telecommunications), Fourth edition (2001-01), IEC 50 (Now: IEC 60050). The references are taken from the current editions of IEC 60050 (845), IEC 60747-5-1 and IEC 60747-5-2. Measurement conditions are based on IEC and other international standards and especially guided by IEC 60747-5-3.

**Editorial notes:** Due to typographical limitations variables cannot be printed in an italics format, which is usually mandatory. Our booklet in general is using American spelling. International standards are written in UK English. Definitions are copied without changes from the original text. Therefore these may contain British spelling.

#### **Radiant and Luminous Quantities and Their Units**

These two kinds of quantities have the same basic symbols, identified respectively, where necessary, by the subscript e (energy) or v (visual), e.g.  $\Phi_{\text{e}}$ ,  $\Phi_{\text{v}}$ . See note.

Note: Photopic and scotopic quantities. Luminous (photometric) quantities are of two kinds, those used for photopic vision and those used for scotopic vision. The wording of the definitions in the two cases being almost identical, a single definition is generally sufficient with the appropriate adjective, photopic or scotopic added where necessary.

The symbols for scotopic quantities are prime ( $\Phi'_{v}$ ,  $I'_{v}$ , etc), but the units are the same in both cases.

In general, optical radiation is measured in radiometric units. Luminous (photometric) units are used when optical radiation is weighted by the sensitivity of the human eye, correctly spoken, by the CIE standard photometric observer (Ideal observer having a relative spectral responsivity curve that conforms to the  $V(\lambda)$  function for photopic vision or to the  $V'(\lambda)$  function for scotopic vision, and that complies with the summation law implied in the definition of luminous flux).

Note: With a given spectral distribution of a radiometric quantity the equivalent photometric quantity can be evaluated. However, from photometric units without knowing the radiometric spectral distribution in general one cannot recover the radiometric quantities.

#### Radiometric Terms, Quantities and Units

The radiometric terms are used to describe the quantities of optical radiation.

The relevant radiometric units are:

TABLE 1 - RADIOMETRIC QUANTITIES AND UNITS							
RADIOMETRIC TERM	SYMBOL	UNIT	REFERENCE				
Radiant power, radiant flux	Фе	W	IEC 50 (845-01-24)				
Radiant intensity	l <sub>e</sub>	W/sr	IEC 50 (845-01-30)				
Irradiance	E <sub>e</sub>	W/m <sup>2</sup>	IEC 50 (845-01-37)				
Radiant exitance	M <sub>e</sub>	W/m <sup>2</sup>	IEC 50 (845-01-47)				
Radiance	L <sub>e</sub>	W/(sr · m <sup>2</sup> )	IEC 50 (845-01-34)				

#### **Photometric Terms, Quantities and Units**

The photometric terms are used to describe the quantities of optical radiation in the wavelength range of visible radiation (generally assumed as the range from 380 nm to 780 nm). The relevant photometric terms are:

TABLE 2 - PHOTOMETRIC QUANTITIES AND UNITS									
PHOTOMETRIC TERM	EQUIVALENT RADIOMETRIC TERM	SYMBOL	UNIT	REFERENCE					
Luminous power	Radiant power		lm	Φ <sub>v</sub> : IEC 50 (845-01-25)					
or luminous flux	or radiant flux $\Phi_{e}$	$\Phi_{\sf V}$		lm: IEC 50 (845-01-51)					
Luminous intensity	Radiant intensity I <sub>e</sub>	I <sub>v</sub>	lm/sr = cd	I <sub>v</sub> : IEC 50 (845-01-31) cd: IEC 50 (845-01-50)					
Illuminance	Irradiance E <sub>e</sub>	E <sub>v</sub>	$Im/m^2 = Ix (Iux)$	E <sub>v</sub> : IEC 50 (845-01-38) lx: IEC 50 (845-01-52)					
Luminous exitance	Radiant exitance M <sub>e</sub>	$M_{v}$	lm/m <sup>2</sup>	IEC 50 (845-01-48)					
Luminance	Radiance L <sub>e</sub>	$L_v$	cd/m <sup>2</sup>	IEC 50 (845-01-35)					

Photometric units are derived from the radiometric units by weighting them with a wavelength dependent standardized human eye sensitivity  $V(\lambda)$  - function, the so-called CIE-standard photometric observer. There are different functions for photopic vision  $(V(\lambda))$  and scotopic vision  $(V'(\lambda))$ .

In the following is shown, how the luminous flux is derived from the radiant power and its spectral distribution. The equivalent other photometric terms can be derived from the radiometric terms in the same way.

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# Relation between distance r, irradiance (illuminance) $E_e$ (E\_V) and intensity $I_e$ (I\_V)

The relation between intensity of a source and the resulting irradiance in the distance r is given by the basic square root rule law.

An emitted intensity  $I_e$  generates in a distance r the irradiance  $E_e = I_e/r^2$ .

This relationship is not valid under near field conditions and should be used not below a distance d smaller than 5 times the emitter source diameter.

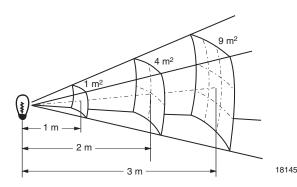


Fig. 2

Using a single radiation point source, one gets the following relation between the parameter  $E_e, \Phi_e, r$ :

$$E_{e} = \frac{d\Phi_{e}}{dA} \left[ \frac{W}{m^{2}} \right]$$

use

$$\mbox{I}_{e} \, = \, \frac{\mbox{d} \Phi}{\mbox{d} \Omega} \, \ , \ \ \Omega \, = \, \frac{\mbox{A}}{\mbox{r}^{2}} \ \ \mbox{and get}$$

$$\mathsf{E}_{e} \,=\, \frac{\mathsf{d}\Phi_{e}}{\mathsf{d}\mathsf{A}} \,=\, \mathsf{I}_{e} \frac{\mathsf{d}\Omega}{\mathsf{d}\mathsf{A}} \,=\, \frac{\mathsf{I}_{e}}{r^{2}_{}} \!\! \left[ \frac{\mathsf{W}}{\mathsf{m}^{2}} \right]$$

#### **Examples**

- 1.Calculate the irradiance with given intensity and distance r: Transceivers with specified intensity of  $I_e$  = 100 mW/sr will generate in a distance of 1m an irradiance of  $E_e$  = 100/1<sup>2</sup> = 100 mW/m<sup>2</sup>. In a distance of 10 m the irradiance would be  $E_e$  = 100/10<sup>2</sup> = 1 mW/m<sup>2</sup>.
- 2.Calculate the range of a system with given intensity and irradiance threshold. When the receiver is specified with a sensitivity threshold irradiance  $E_e=20~\text{mW/m}^2$ , the transmitter with an intensity  $I_e=120~\text{mW/s}$ r the resulting range can be calculated as

$$r = \sqrt{\frac{I_e}{E_e}} = \sqrt{\frac{120}{20}} = \sqrt{6} = 2.45 \text{ m}$$